

IN THE CLAIMS

Please amend the claims as follows:

Please add new claim 20.

Please amend claims 15, 17, and 18 as follows:

1-12. (Cancelled)

13. (original) A method for fabricating a semiconductor device using an ArF exposure light source, comprising the steps of:

forming a conducting layer on a semiconductor substrate;

forming a first hard mask layer and a second hard mask layer on the conducting layer in order;

forming a photoresist pattern on the second hard mask layer using an ArF exposure light source to form a predetermined pattern;

forming a first hard mask pattern by etching the second hard mask layer using the photoresist pattern as an etching mask;

etching the first hard mask layer using at least the first hard mask pattern and forming a second hard mask pattern, thereby forming a first resulting structure;

depositing an insulation layer on the first resulting structure; and

patternning the conducting layer using the second hard mask pattern as an etching mask.

14. (original) The method in accordance with claim 13, wherein the insulation layer is one of a flowable insulation layer and an organic polymer.

15. (currently amended) The method in accordance with claim ~~13~~<sup>14</sup>, wherein the first hard mask layer is a nitride layer and the second hard mask layer is a conducting layer which is one of a tungsten layer and a tungsten nitride layer.

16. (original) The method in accordance with claim 15, wherein the flowable insulation layer is one of a SOG layer and an APL layer.

17. (currently amended) The method in accordance with claim ~~14~~<sup>1420</sup>, wherein the step of removing the insulation layer and the first hard mask pattern includes the steps of:

applying a first wet etching process using a fluoride solution to remove a portion of the insulation layer;

applying a second wet etching process using an SC-1 solution to remove the first hard mask pattern; and

applying a third wet etching process using the fluoride solution to remove the residual of the first hard mask pattern.

18. (currently amended) The method in accordance with claim 14, further comprising the step of forming an antireflective coating layer on the ~~third~~<sup>second</sup> hard mask layer.

19. (original) The method in accordance with claim 13, wherein the predetermined pattern is one of a gate electrode pattern, a bit line pattern and a metal line pattern.

20. (New) The method in accordance with claim 13, further comprising the step of removing the insulation layer and the first hard mask pattern.